

THIN FILM TRANSISTOR AND METHOD FOR MANUFACTURING SAME
ABSTRACT OF THE DISCLOSURE

A TFT (Thin Film Transistor) is provided in which a hydrogen feeding layer is able to be formed in a position where diffusing distance of hydrogen can be made short without causing an increase
5 in photolithography processes. In the TFT, the hydrogen feeding layer to diffuse hydrogen into a dangling bond existing at an interface between a polycrystalline silicon thin film and a gate insulating film is formed in a position between the gate
10 insulating film and a gate electrode. According to this configuration, diffusing distance of hydrogen at a period of time during hydrogenation can be made short and the hydrogenation process can be sufficiently performed without taking time in heat treatment.

FIG. 1